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Abstract

Method and Apparatus for forming a film on a substrate.

This invention relates to a method and apparatus for forming a film on the substrate. The method comprises supplying to the chamber in gaseous or vapour form a silicon containing organic compound and an oxidising agent in the presence of a plasma to deposit a film on the substrate and setting the film such that carbon containing groups are retained therein. In particular embodiments the setting is achieved by exposing the film to $\rm H_2$ plasma.

Figure 1.